**Product data sheet** 

# 1. General description

NPN low  $V_{CEsat}$  transistor in a small SOT89 (SC-62/TO-243) Surface Mounted Device (SMD) plastic package.

PNP complement: PBSS9110X-Q.

# 2. Features and benefits

- SOT89 package
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- High efficiency leading to less heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

# 3. Applications

- · Major application segments:
  - Automotive 42 V power
  - · Telecom infrastructure
  - Industrial
- Peripheral driver:
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - Inductive load driver (e.g. relays, buzzers and motors)
- DC-to-DC converter

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	100	V
I <sub>C</sub>	collector current		-	-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	3	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	165	200	mΩ



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# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector	1 1	
3	В	base	3 2 1	B → , , , , , , , , , , , , , , , , , ,
			SOT89	sym123

# 6. Marking

### Table 3. Marking codes

Type number	Marking code[1]
PBSS8110X-Q	%4B

[1] % = placeholder for manufacturing site code

# 7. Limiting values

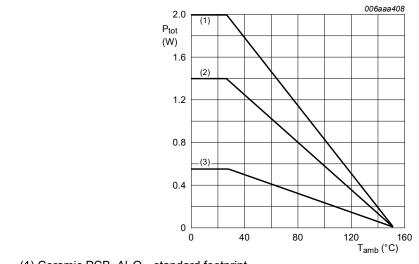
#### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	120	V
$V_{CEO}$	collector-emitter voltage	open base		-	100	V
$V_{EBO}$	emitter-base voltage	open collector		-	5	V
Ic	collector current			-	1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	3	Α
I <sub>B</sub>	base current			-	300	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.55	W
			[2]	-	1.4	W
			[3]	-	2	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB; mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB; standard footprint

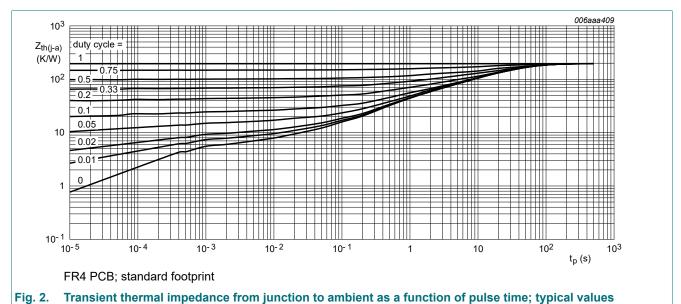
**Power derating curves** Fig. 1.

## Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	227	K/W
	junction to ambient		[2]	-	-	89	K/W
			[3]	-	-	63	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



### 100 V, 1 A NPN low VCEsat transistor

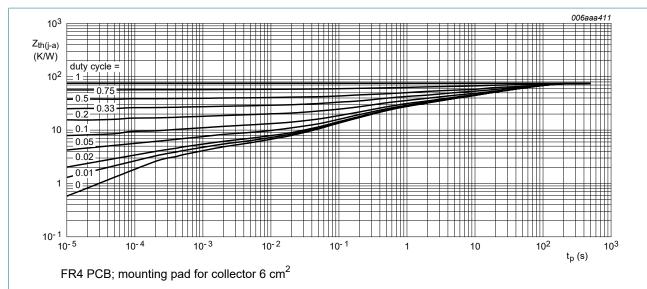


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

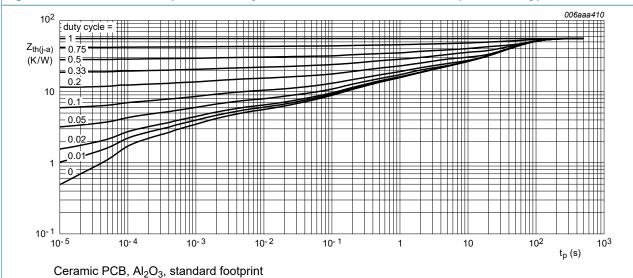


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

## 9. Characteristics

**Table 6. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 80 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 1 mA; T <sub>amb</sub> = 25 °C	150	-	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 250 mA; $T_{amb}$ = 25 °C	150	-	500	
		$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	-	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 1 A; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	80	-	-	

### 100 V, 1 A NPN low VCEsat transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 10 mA; T <sub>amb</sub> = 25 °C	-	-	40	mV
	saturation voltage	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	-	120	mV
		$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le$	-	-	200	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	165	200	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA; T <sub>amb</sub> = 25 °C	-	-	1.05	V
$V_{BEon}$	base-emitter turn-on voltage	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 1 A; T <sub>amb</sub> = 25 °C	-	-	0.9	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 10 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 0.025 A;	-	25	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.025 A; T <sub>amb</sub> = 25 °C	-	220	-	ns
t <sub>on</sub>	turn-on time		-	245	-	ns
t <sub>s</sub>	storage time		-	365	-	ns
t <sub>f</sub>	fall time		-	185	-	ns
t <sub>off</sub>	turn-off time		-	550	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	-	7.5	pF

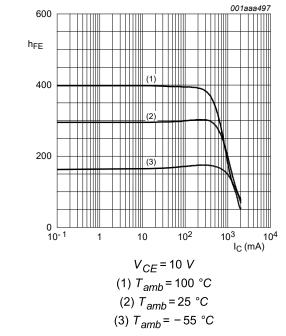


Fig. 5. DC current gain as a function of collector current; typical values

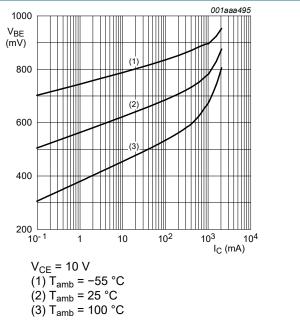
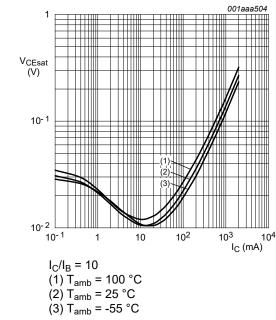


Fig. 6. Base-emitter voltage as a function of collector current; typical values

### 100 V, 1 A NPN low VCEsat transistor



$$(1) T_{amb} = 100 °($$

Fig. 7. Collector-emitter saturation voltage as a

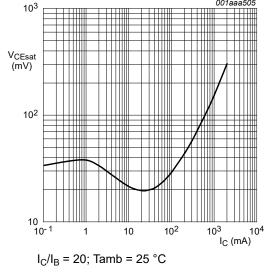


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

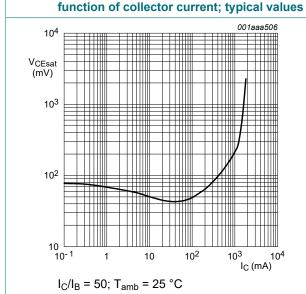
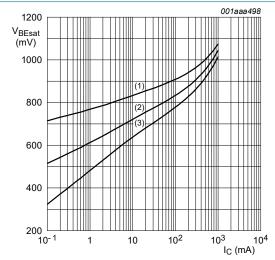


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=10$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

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### 100 V, 1 A NPN low VCEsat transistor

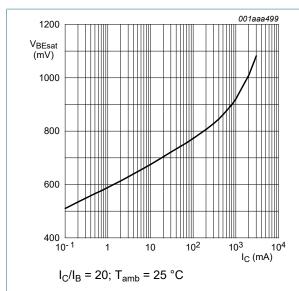
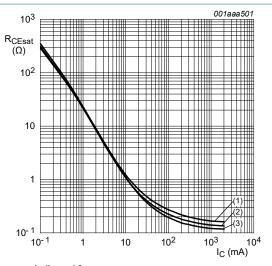


Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values



$$I_{C}/I_{B} = 10$$
  
(1)  $T_{amb} = 100 \,^{\circ}C$   
(2)  $T_{amb} = 25 \,^{\circ}C$   
(3)  $T_{amb} = -55 \,^{\circ}C$ 

$$(3) T_{amb} = -55 °C$$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

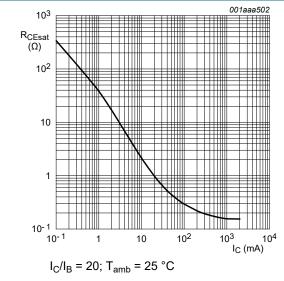


Fig. 13. Equivalent on-resistance as a function of collector current; typical values

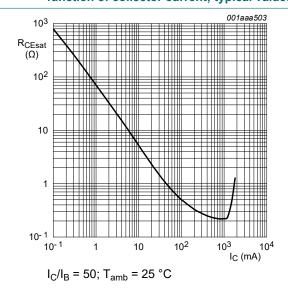
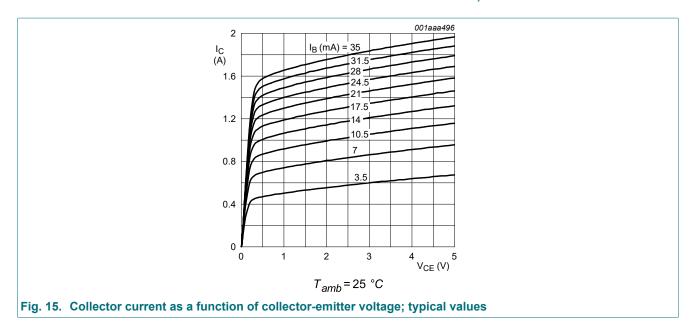
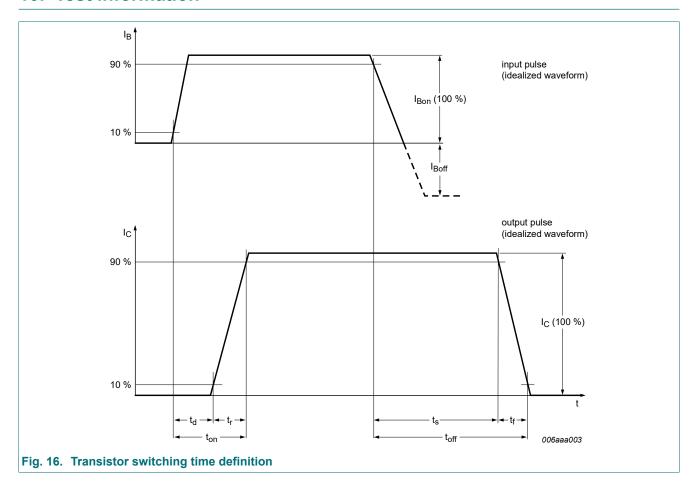


Fig. 14. Equivalent on-resistance as a function of collector current; typical values

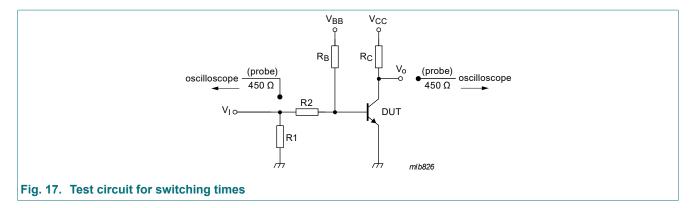
## 100 V, 1 A NPN low VCEsat transistor



# 10. Test information



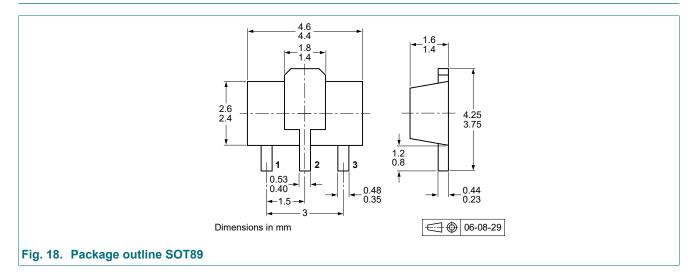
### 100 V, 1 A NPN low VCEsat transistor



## **Quality information**

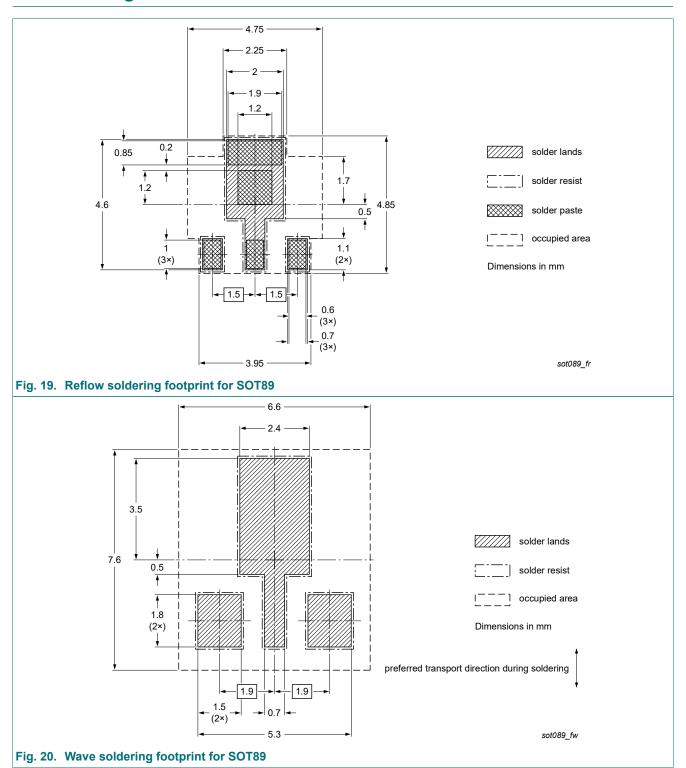
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 11. Package outline



100 V, 1 A NPN low VCEsat transistor

# 12. Soldering



100 V, 1 A NPN low VCEsat transistor

# 13. Revision history

### **Table 7. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS8110X-Q v.1	20250704	Product data sheet	-	-

### 100 V, 1 A NPN low VCEsat transistor

# 14. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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